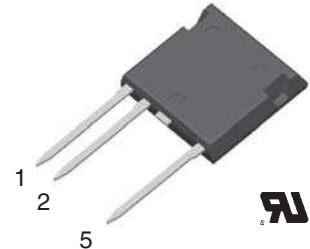
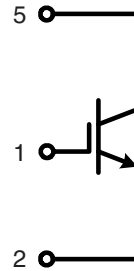


High Voltage IGBT

in High Voltage
ISOPLUS i4-PAC™

$I_{C25} = 32\text{ A}$
 $V_{CES} = 2500\text{ V}$
 $V_{CE(sat)} = 3.2\text{ V}$
 $t_f = 250\text{ ns}$



IGBT

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$	2500	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^\circ\text{C}$	32	A
I_{C90}	$T_C = 90^\circ\text{C}$	19	A
I_{CM}	$V_{GE} = \pm 15\text{ V}; R_G = 47\ \Omega; T_{VJ} = 125^\circ\text{C}$	70	A
V_{CEK}	RBSOA, Clamped inductive load; $L = 100\ \mu\text{H}$	1200	V
P_{tot}	$T_C = 25^\circ\text{C}$	250	W

Features

- High Voltage IGBT
 - substitute for high voltage MOSFETs with significantly lower voltage drop and comparable switching speed
 - substitute for high voltage thyristors with voltage control of turn on & turn off
 - substitute for electromechanical trigger and discharge relays
- ISOPLUS i4-PAC™ high voltage package
 - isolated back surface
 - enlarged creepage towards heatsink
 - enlarged creepage between high voltage pins
 - application friendly pinout
 - high reliability
 - industry standard outline
 - UL registered E72873

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 19\text{ A}; V_{GE} = 15\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		3.2 4.7	V V	
$V_{GE(th)}$	$I_C = 1\text{ mA}; V_{GE} = V_{CE}$	5		8 V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.2	0.15 mA mA	
I_{GES}	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			500 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 1500\text{ V}; I_C = 19\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 47\ \Omega$		100 50 600 250 15 30	ns ns ns ns mJ mJ	
C_{ies} C_{oes} C_{res}		$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		2.28 103 43	nF pF pF
Q_{Gon}			$V_{CE} = 1500\text{ V}; V_{GE} = 15\text{ V}; I_C = 19\text{ A}$	142	nC
R_{thJC}					0.5 K/W

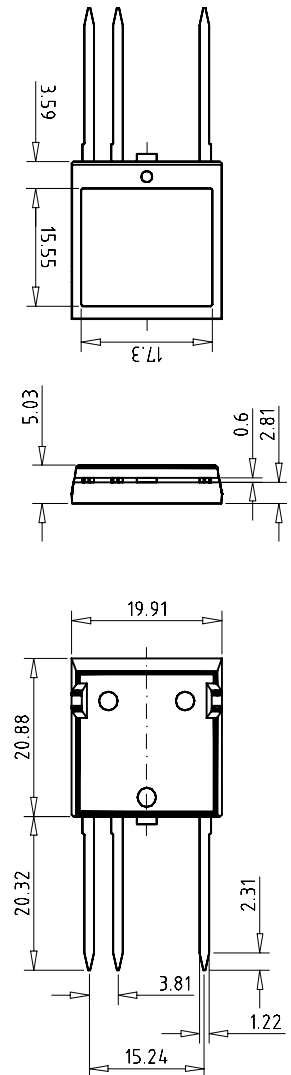
Applications

- switched mode power supplies
- DC-DC converters
- resonant converters
- laser generators, x ray generators
- discharge circuits

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	°C
T_{stg}		-55...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
F_c	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s, d_A	C pin - E pin	7.0		mm
d_s, d_A	pin - backside metal	5.5		mm
R_{thCH}	with heatsink compound		0.15	K/W
Weight			9	g

Dimensions in mm (1 mm = 0.0394")


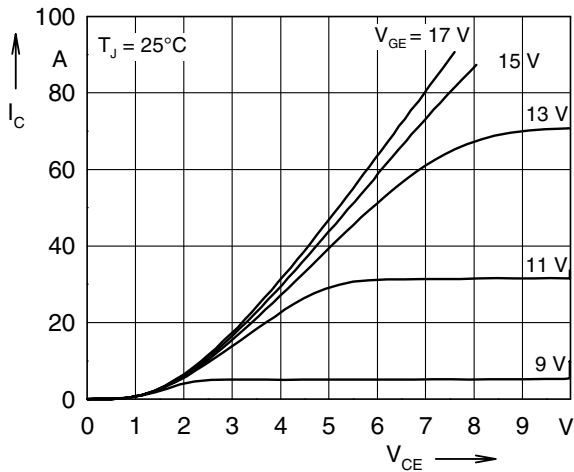


Fig. 1 Typ. Output Characteristics

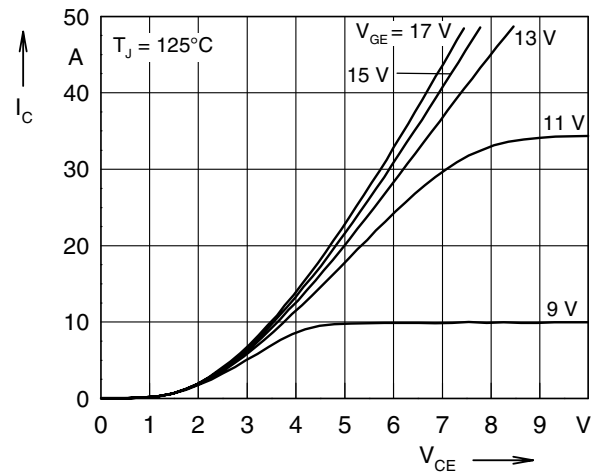


Fig. 2 Typ. Output Characteristics

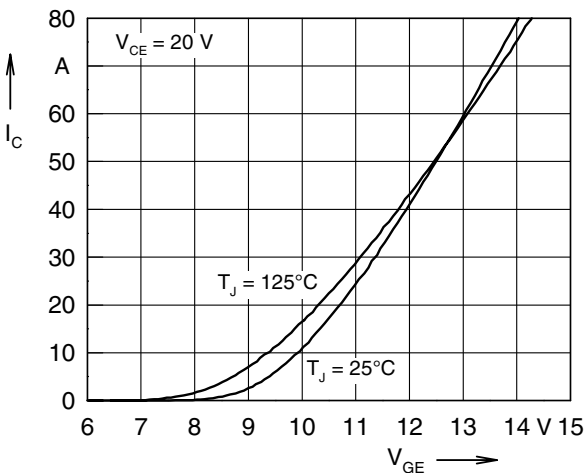


Fig. 3 Typ. Transfer Characteristics

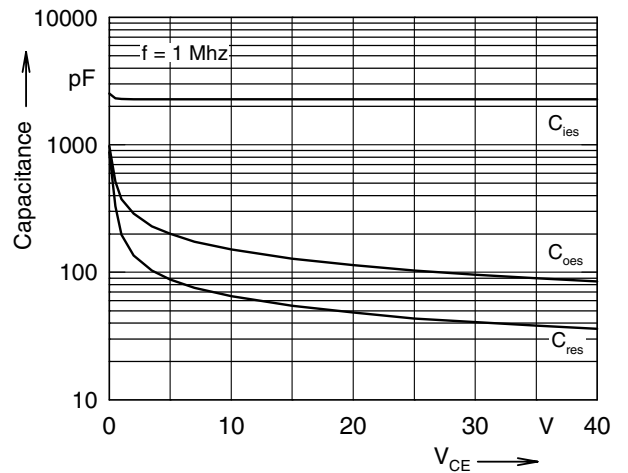


Fig. 4 Capacitance curves

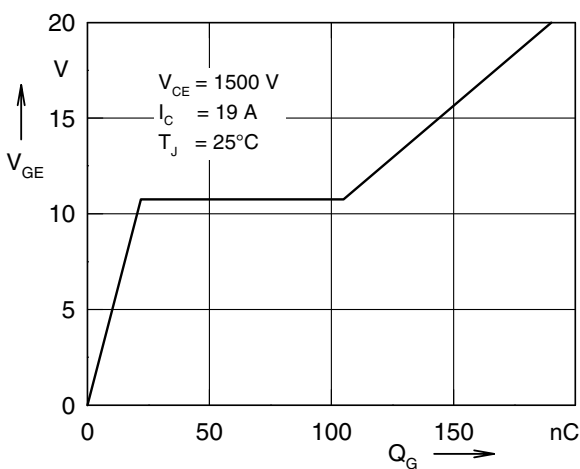


Fig. 5 Typ. Gate Charge characteristics

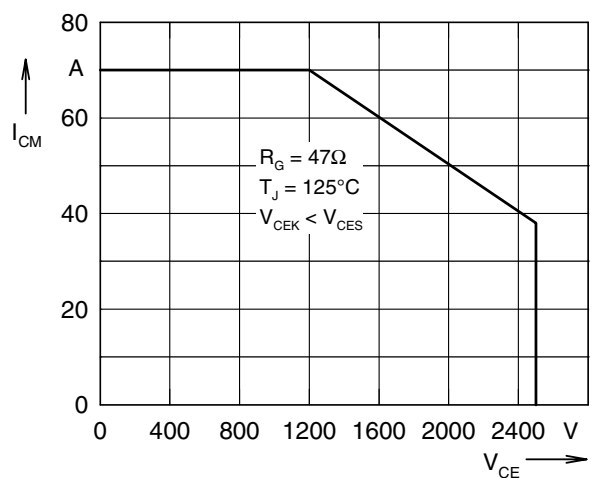


Fig. 6 Reverse Biased Safe Operating Area RBSOA

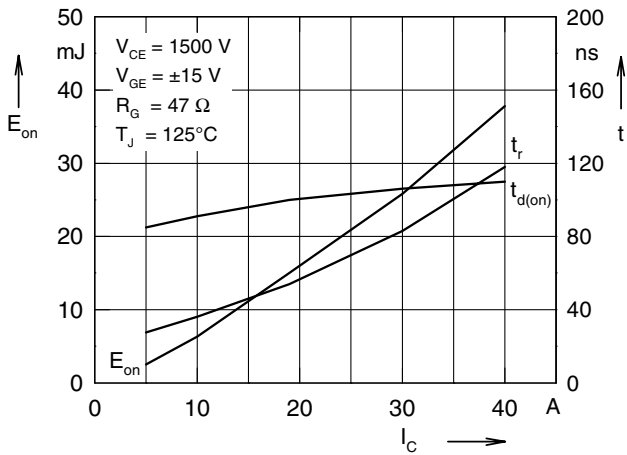


Fig. 7 Typ. turn on energy and switching times versus collector current

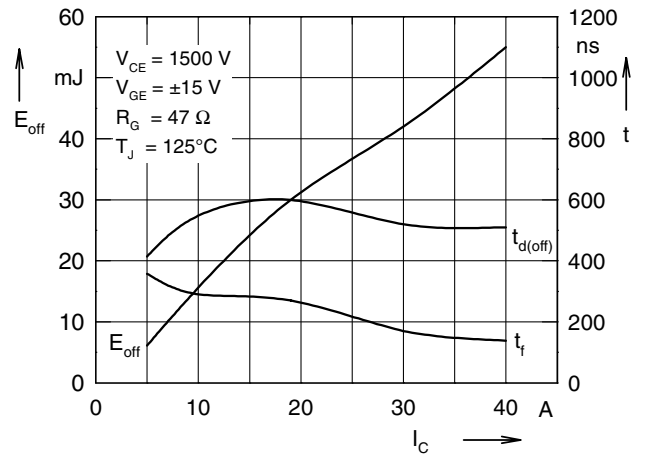


Fig. 8 Typ. turn off energy and switching times versus collector current

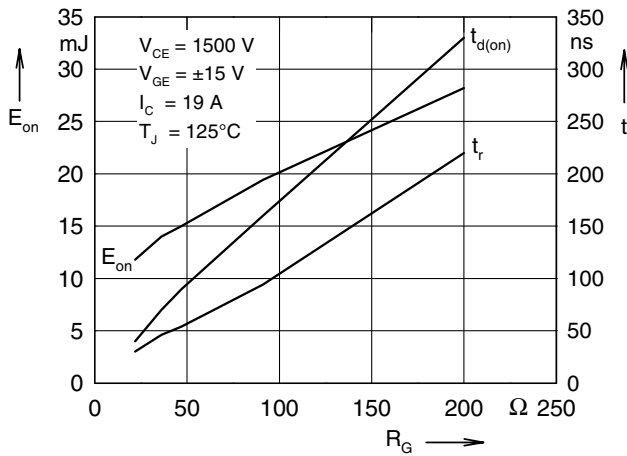


Fig. 9 Typ. turn on energy and switching times versus gate resistor

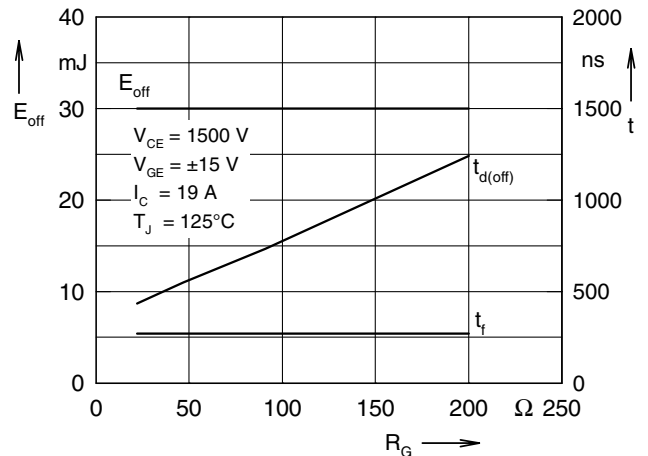


Fig. 10 Typ. turn off energy and switching times versus gate resistor

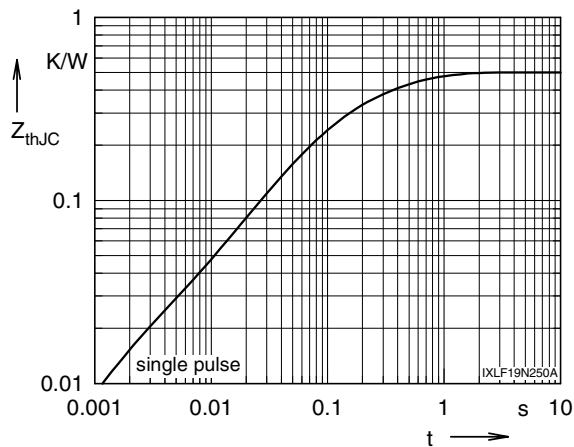


Fig. 11 Typ. transient thermal impedance